

Title (en)

OPTOELECTRONIC SEMICONDUCTOR COMPONENT AND PRODUCTION METHOD

Title (de)

OPTOELEKTRONISCHES HALBLEITERBAUELEMENT UND VERFAHREN ZUR HERSTELLUNG

Title (fr)

COMPOSANT À SEMI-CONDUCTEUR OPTOÉLECTRONIQUE ET SON PROCÉDÉ DE FABRICATION

Publication

**EP 4214763 A1 20230726 (DE)**

Application

**EP 21773576 A 20210908**

Priority

- DE 102020124258 A 20200917
- EP 2021074706 W 20210908

Abstract (en)

[origin: WO2022058217A1] An optoelectronic semiconductor component (16) is specified, comprising a layer stack (9) comprising at least one side surface (9A), a first main surface (9B) and a second main surface (90), a first contact means (12) arranged at the first main surface (9B) and provided for electrically contacting a first semiconductor region (4) of the layer stack (9), – a second contact means (17) arranged at the second main surface (90) and provided for electrically contacting a second semiconductor region (5) of the layer stack (9), said second contact means being radiation-transmissive, and an electrically conductive edge layer (11) arranged on the layer stack (9) and extending from the second contact means (17) over the side surface (9A) as far as the first main surface (9B), and – a first dielectric layer (10) arranged between the edge layer (11) and the layer stack (9), the second main surface (90) not being covered by the first dielectric layer (10). Furthermore, a method for producing at least one optoelectronic semiconductor component is specified.

IPC 8 full level

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CPC (source: EP KR US)

**H01L 33/0093** (2020.05 - KR US); **H01L 33/0095** (2013.01 - KR); **H01L 33/20** (2013.01 - EP KR); **H01L 33/405** (2013.01 - KR); **H01L 33/42** (2013.01 - EP KR); **H01L 33/44** (2013.01 - US); **H01L 33/60** (2013.01 - KR); **H01L 33/62** (2013.01 - EP KR US); **H01L 33/0093** (2020.05 - EP); **H01L 33/0095** (2013.01 - EP); **H01L 33/20** (2013.01 - US); **H01L 33/405** (2013.01 - EP); **H01L 33/60** (2013.01 - EP); **H01L 2933/0016** (2013.01 - EP KR); **H01L 2933/0058** (2013.01 - EP KR); **H01L 2933/0066** (2013.01 - EP KR)

Citation (search report)

See references of WO 2022058217A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

Designated validation state (EPC)

KH MA MD TN

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DOCDB simple family (application)

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